

深圳市晶泰源电子有限公司

MMBT5401LTI TRANSISTOR(PNP)

FEATURES

MARKING: 2L

Power dissipation

P_{CM} : 0.3W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -160 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-150V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-130V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-1mA$	80			
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-10mA$	100		200	
	$h_{FE(3)}$	$V_{CE}=-5V, I_C=-50mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50mA, I_B=-5mA$			-1.0	V
Transition frequency	f_T	$V_{CE}=-5V, I_E=-10mA$ $f=30MHz$	80			MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank				
Range	100~200			

深圳市晶泰源电子有限公司

电话：83211536 传真：83206326

地址：华强广场C座11C室